

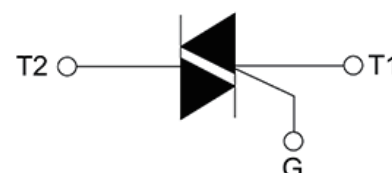
DESCRIPTION:

The chip triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The chip embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III}$	10/10/10	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 106^{\circ}C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		132	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=150^{\circ}C$)	di/dt	100	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=150^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^\circ C$ $R_L=3.3k\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	20	mA
		II		30	
I_H	$I_T=500mA$		MAX.	10	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150^\circ C$		MIN.	200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150^\circ C$		MIN.	1.8	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$		TYP.	3	μs
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ C$	0.75	V
R_D	Dynamic resistance	$T_j=150^\circ C$	37	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=150^\circ C$	1.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ C/W$

FIG : Maximum power dissipation versus RMS on-state current

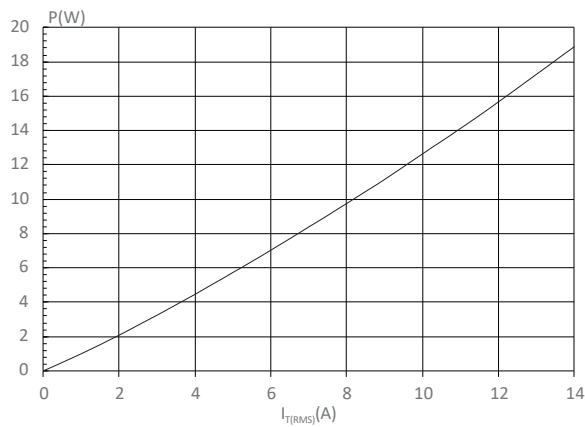


FIG : Surge peak on-state current versus number of cycles

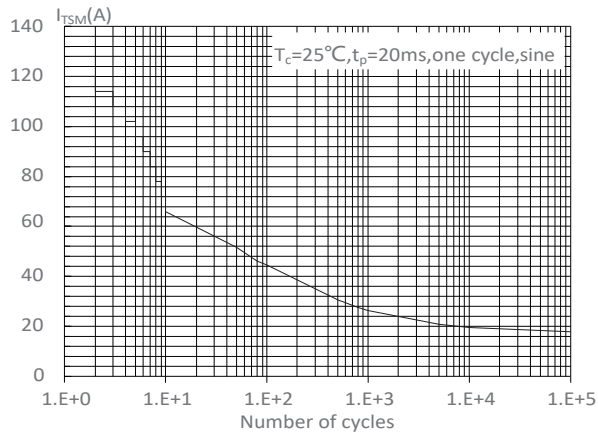


FIG : Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

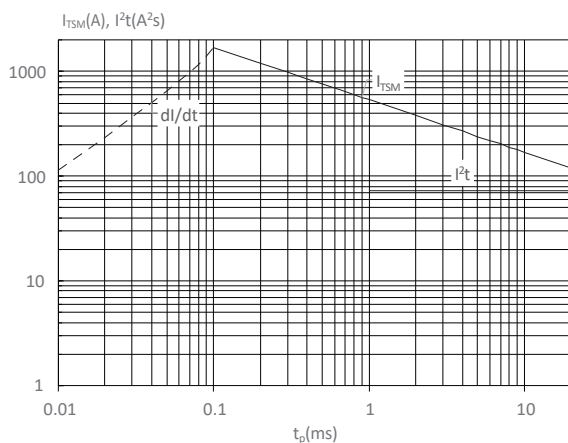


FIG : RMS on-state current versus case temperature

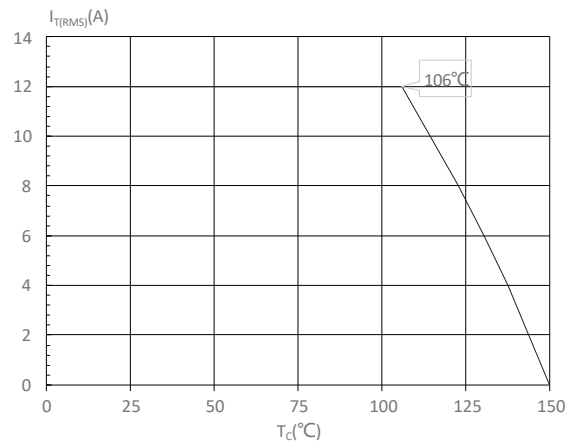


FIG : On-state characteristics

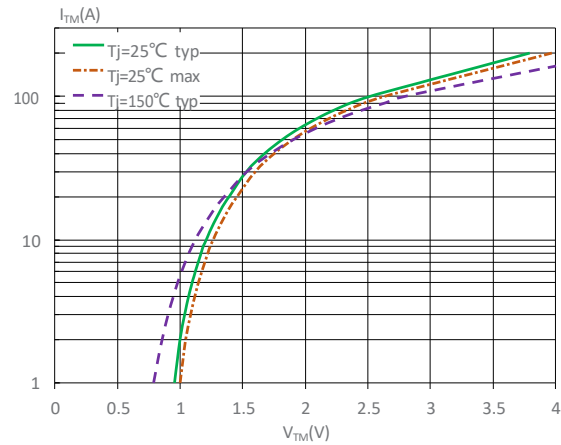


FIG : Relative variations of gate trigger current, holding current and latching current versus junction temperature

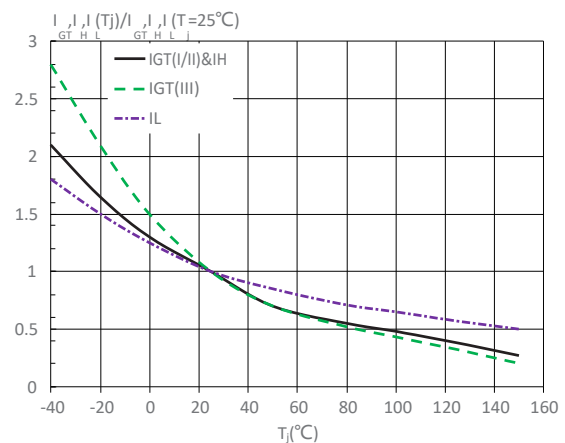
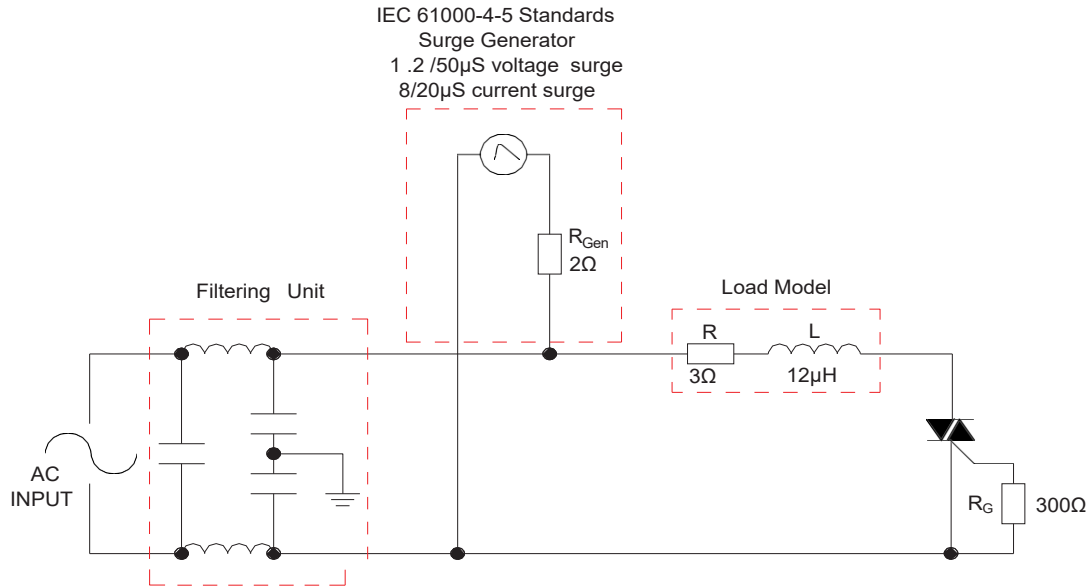


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.